

# FDC606P

## P-Channel 1.8V Specified PowerTrench® MOSFET

### General Description

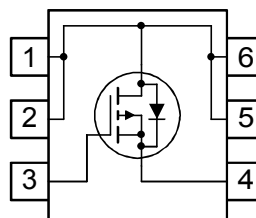
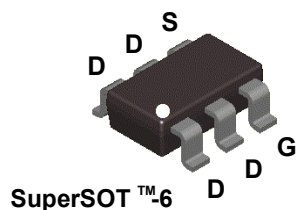
This P-Channel 1.8V specified MOSFET uses Fairchild's low voltage PowerTrench process. It has been optimized for battery power management applications.

### Applications

- Battery management
- Load switch
- Battery protection

### Features

- -6 A, -12 V.  $R_{DS(ON)} = 26\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$   
 $R_{DS(ON)} = 35\text{ m}\Omega @ V_{GS} = -2.5\text{ V}$   
 $R_{DS(ON)} = 53\text{ m}\Omega @ V_{GS} = -1.8\text{ V}$
- Fast switching speed
- High performance trench technology for extremely low  $R_{DS(ON)}$



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	-12	V
$V_{GSS}$	Gate-Source Voltage	$\pm 8$	V
$I_D$	Drain Current – Continuous (Note 1a) – Pulsed	-6	A
		-20	
$P_D$	Maximum Power Dissipation (Note 1a) (Note 1b)	1.6	W
		0.8	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	30	$^\circ\text{C/W}$

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.606	FDC606P	7"	8mm	3000 units

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-12			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-3		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
$I_{GSSF}$	Gate–Body Leakage, Forward	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate–Body Leakage, Reverse	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
<b>On Characteristics (Note 2)</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.4	-0.5	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		2.5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5\text{ V}, I_D = -6\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -5\text{ A}$ $V_{GS} = -1.8\text{ V}, I_D = -4\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -6\text{ A}, T_J = 125^\circ\text{C}$		21 26 34 28	26 35 53 35	m $\Omega$
$I_{D(on)}$	On–State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-20			A
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -6\text{ A}$		25		S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -6\text{ V}, V_{GS} = 0\text{ V},$		1699		pF
$C_{oss}$	Output Capacitance	$f = 1.0\text{ MHz}$		679		pF
$C_{rss}$	Reverse Transfer Capacitance			423		pF
<b>Switching Characteristics (Note 2)</b>						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -6\text{ V}, I_D = -1\text{ A},$		11	19	ns
$t_r$	Turn–On Rise Time	$V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		10	20	ns
$t_{d(off)}$	Turn–Off Delay Time			89	142	ns
$t_f$	Turn–Off Fall Time			70	112	ns
$Q_g$	Total Gate Charge	$V_{DS} = -6\text{ V}, I_D = -6\text{ A},$		18	25	nC
$Q_{gs}$	Gate–Source Charge	$V_{GS} = -4.5\text{ V}$		3		nC
$Q_{gd}$	Gate–Drain Charge			4.2		nC
<b>Drain–Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain–Source Diode Forward Current				-1.3	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -1.3\text{ A}$ (Note 2)		-0.6	-1.2	V

**Notes:**

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.
  - 78 $^\circ\text{C}/\text{W}$  when mounted on a 1in<sup>2</sup> pad of 2oz copper on FR-4 board.
  - 156 $^\circ\text{C}/\text{W}$  when mounted on a minimum pad.
- Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

## Typical Characteristics

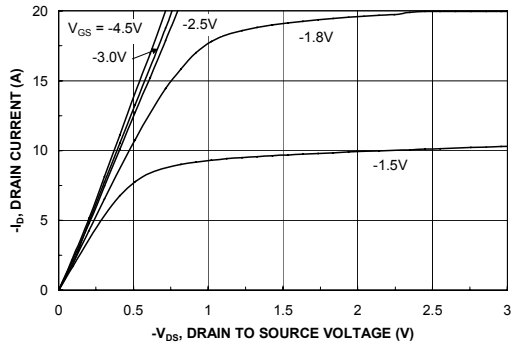


Figure 1. On-Region Characteristics.

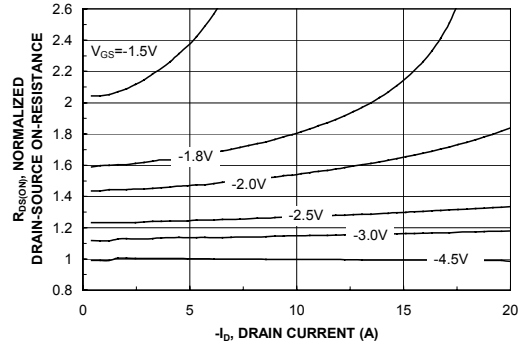


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

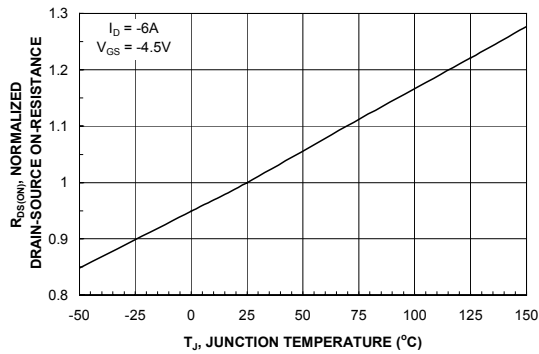


Figure 3. On-Resistance Variation with Temperature.

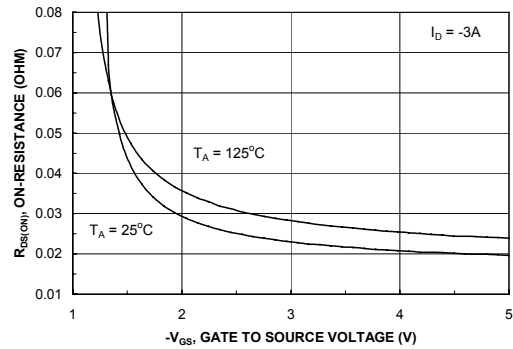


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

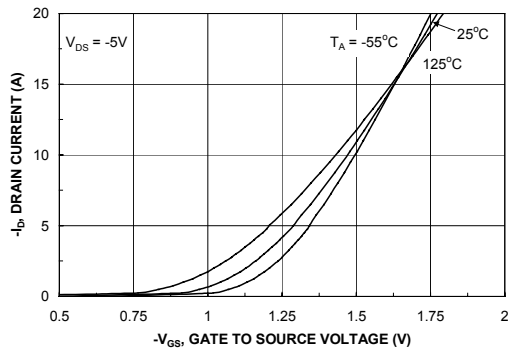


Figure 5. Transfer Characteristics.

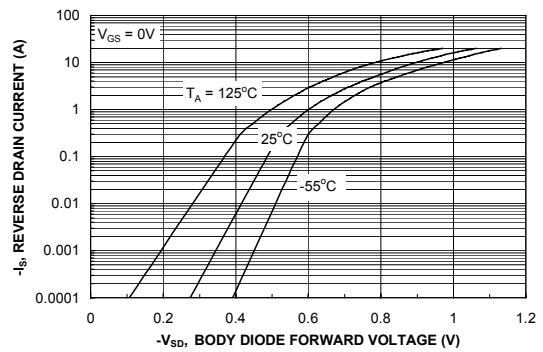
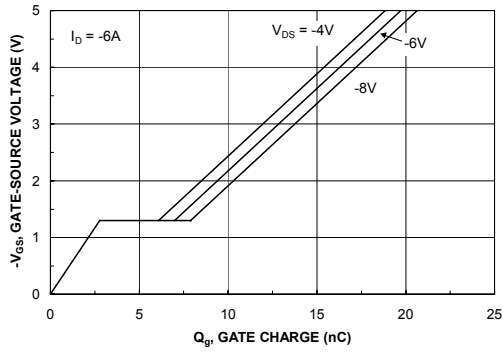
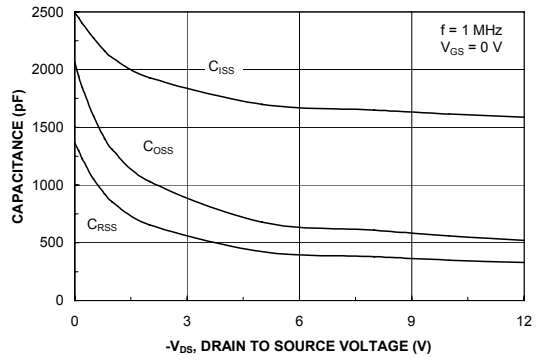


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

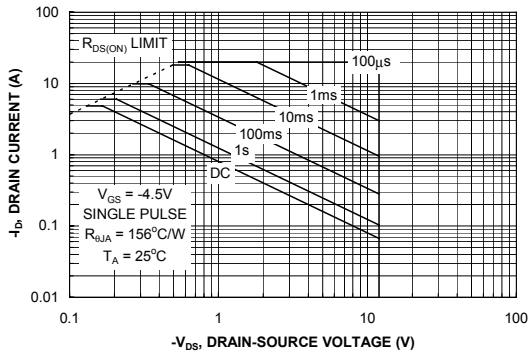
### Typical Characteristics



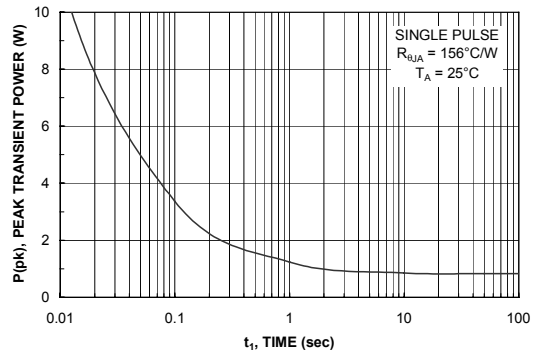
**Figure 7. Gate Charge Characteristics.**



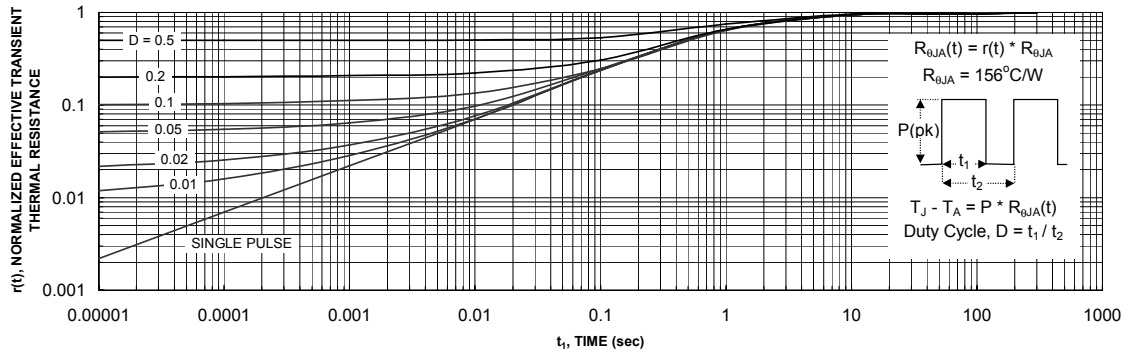
**Figure 8. Capacitance Characteristics.**



**Figure 9. Maximum Safe Operating Area.**



**Figure 10. Single Pulse Maximum Power Dissipation.**



**Figure 11. Transient Thermal Response Curve.**

Thermal characterization performed using the conditions described in Note 1b.  
Transient thermal response will change depending on the circuit board design.

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